TOSHIBA Photocoupler GaAs IRed & Photo-Transistor

4N25(Short),4N25A(Short),4N26(Short),4N27(Short),4N28(Short)

AC Line / Digital Logic Isolator.

Digital Logic / Digital Logic Isolator.

Telephone Line Receiver.

Twisted Pair Line Receiver

High Frequency Power Supply Feedback Control.

Relay Contact Monitor.

The TOSHIBA 4N25 (Short) through 4N28 (Short) consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor in a dual in–line package.

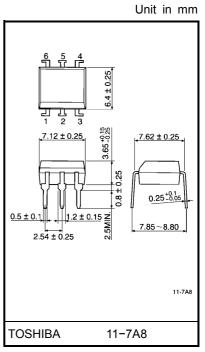
• Switching speeds: 3µs (typ.)

• DC current transfer ratio: 100% (typ.)

• Isolation resistance: $10^{11}\Omega$ (min.)

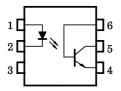
• Isolation voltage: 2500Vrms (min.)

• UL recognized: UL1577, file No. E67349



Weight: 0.4g

Pin Configurations(top view)



1:ANODE

2: CATHODE

3 : N.C.

4:EMITTER

5 : COLLECTOR

6 : BASE



Maximum Ratings (Ta = 25°C)

| | Characteristic | Symbol | Rating | Unit |
|----------|--|----------------------|----------|---------|
| LED | Forward current (continuous) | IF | 80 | mA |
| | Forward current derating | ΔI _F / °C | 1.07 (*) | mA / °C |
| | Peak forward current (Note 1) | I _{PF} | 3 | Α |
| | Power dissipation | P _D | 150 | mW |
| | Power dissipation derating | ΔP _D / °C | 2.0 (*) | mW / °C |
| | Reverse voltage | V _R | 3 | V |
| | Collector-emitter voltage | BV _{CEO} | 30 | V |
| Detector | Collector-base voltage | BV _{CBO} | 70 | V |
| | Emitter–collector voltage | BV _{ECO} | 7 | V |
| | Collector current (continuous) | IC | 100 | mA |
| | Power dissipation | PC | 150 | mW |
| | Power dissipation derating | ΔP _C / °C | 2.0 (*) | mW / °C |
| | Storage temperature range | T _{stg} | -55~150 | °C |
| _ | Operating temperature range | T _{opr} | -55~100 | °C |
| Coupled | Lead soldering temperature (10s) | T _{sol} | 260 | °C |
| | Total package power dissipation | P _T | 250 | mW |
| | Total package power dissipation derating | ΔP _T / °C | 3.3 (*) | mW / °C |

(Note 1) Pulse width 300µs, 2% duty cycle.

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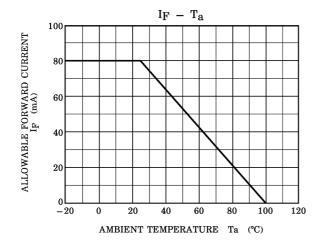
^(*) Above 25°C ambient.

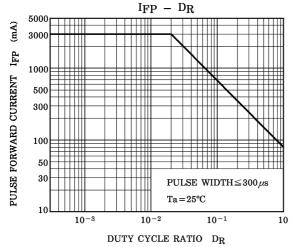


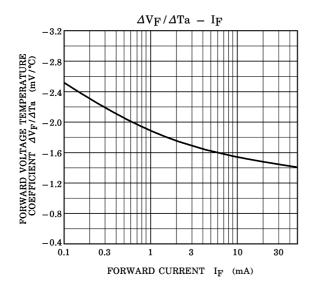
Electrical Characteristics (Ta = 25°C)

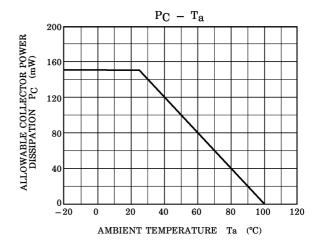
| Characteristic | | | Symbol | Test Condition | Min. | Тур. | Max. | Unit |
|----------------|--------------------------------------|-------------|---------------------------------|--|------------------|------|------|------|
| LED | Forward voltage | | V _F | I _F = 10 mA | _ | 1.15 | 1.5 | V |
| | Reverse current | | I _R | V _R = 3 V | _ | _ | 100 | μA |
| | Capacitance | | C _D | V = 0, f = 1 MHz | _ | 30 | _ | pF |
| Detector | DC forward current gain | | h _{FE} | V _{CE} = 5V, I _C = 500 μA | _ | 200 | _ | _ |
| | Collector-emitter breakdown voltage | | V (BR) CEO | I _C = 1 mA, I _F = 0 | 30 | _ | _ | V |
| | Collector-base breakdown voltage | | V (BR) CBO | I _C = 100 μA | 70 | _ | _ | V |
| | Emitter–collector breakdown voltage | | V (BR) ECO | ΙΕ = 100 μΑ | 7 | _ | _ | V |
| | Collector dark current | | I _{CEO} | V _{CE} = 10 V | _ | 1 | 50 | nA |
| | Collector dark current | | I _{CBO} | V _{CB} = 10 V | _ | 0.1 | 20 | nA |
| | Collector-emitter capacitance | | C _{CE} | V = 0, f = 1 MHz | _ | 10 | _ | pF |
| pa | Current transfer ratio | | I _C / I _F | I _F = 10 mA, V _{CE} = 10 V | 20 | 100 | _ | % |
| | Collector–emitter saturation voltage | | V _{CE (sat)} | I _F = 50 mA, I _C = 2 mA | _ | 0.1 | 0.5 | V |
| | Capacitance input to output | | CS | V _S = 0, f = 1 MHz | _ | 0.8 | _ | pF |
| | Isolation resistance | | R _S | V _S = 500 V, R.H. ≤ 60 % | 10 ¹¹ | _ | _ | Ω |
| | | | BVS | AC, 1 minute | 2500 | _ | _ | Vrms |
| Coupled | Isolation voltage | 4N25, 4N25A | BV _S (*) | AC, peak | 2500 | _ | _ | |
| S | | 4N26, 4N27 | | | 1500 | _ | _ | Vpk |
| | | 4N28 | | | 500 | _ | _ | |
| | | 4N25A | | AC, 1 second | 1775 | _ | _ | Vrms |
| | Rise / fall time | | t _r / t _f | V_{CE} = 10 V, I_{C} = 2 mA R_{L} = 100 Ω | _ | 2 | | μs |
| | Rise / fall time | | t _r / t _f | V _{CB} = 10 V, I _{CB} = 50 μA R _L = 100Ω | _ | 200 | _ | ns |

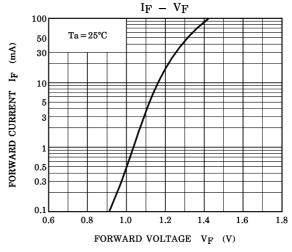
^(*) JEDEC registered minimum BV_S, however, TOSHIBA specifies a minimum BV_S of 2500 Vrms, 1 minute.

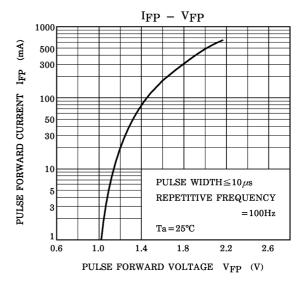




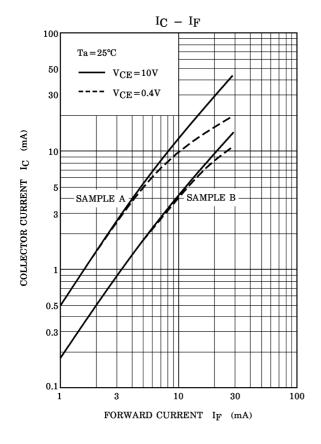


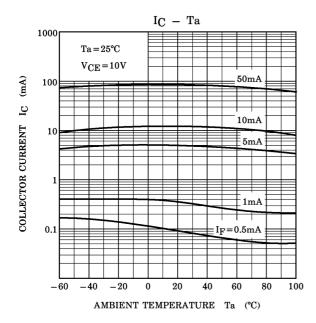


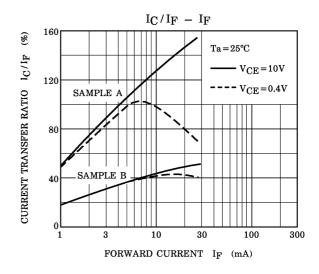


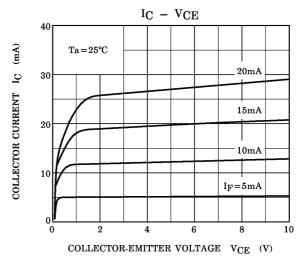


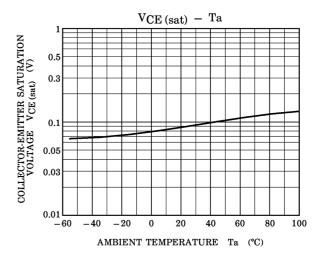
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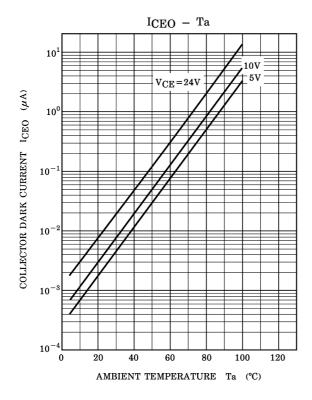


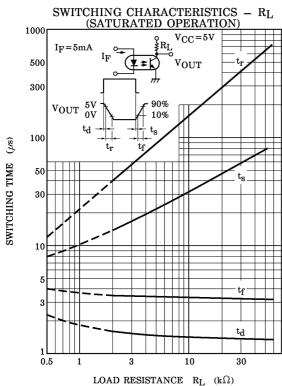


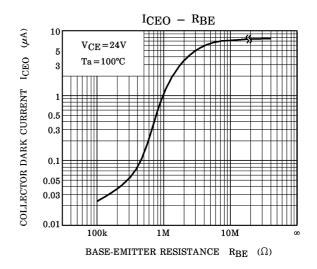


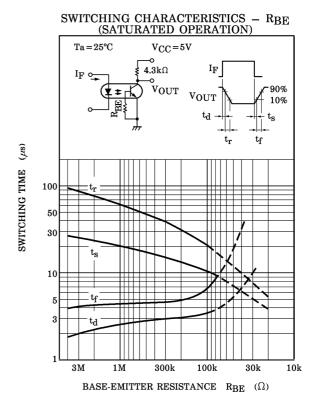












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